



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-02C Plastic-Encapsulate Diodes

DS520-30LED02 Schottky barrier Diodes

DESCRIPTION

Silicon epitaxial planar

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

APPLICATION

High speed switching For Detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

WBFBP-02C

(1.0×0.6×0.5)

unit: mm



MARKING: E



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	100	mA
Peak forward surge current	I _{FSM}	500	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			0.45	V	I _F =10mA
Reverse current	I _R			0.5	μA	V _R =10V

Typical Characteristics

●Electrical characteristic curves (Ta=25°C)

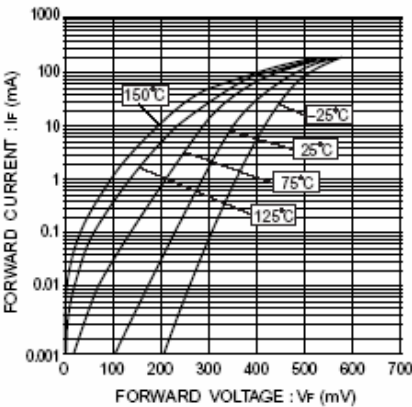


Fig.1 Forward characteristics

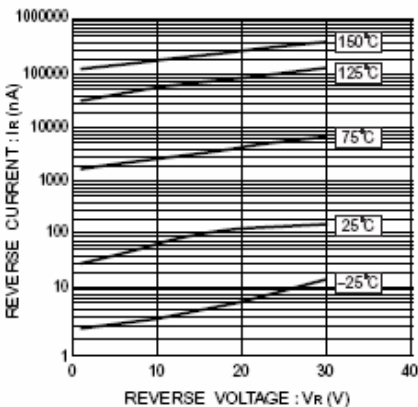


Fig.2 Reverse characteristics

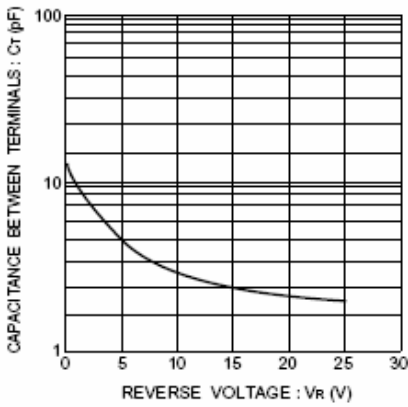


Fig. 3 Capacitance between terminals characteristics